

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

IRF3205STRLPBF

DESCRIPTION

- Drain Current $I_D=110A@T_C=25^{\circ}C$
- Drain Source Voltage
 : V_{DSS}= 55V(Min)
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

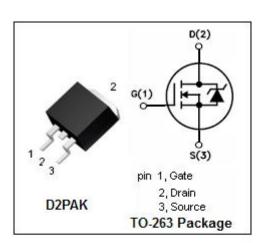
APPLICATIONS

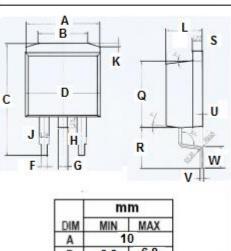
• Designed for high current, high speed switching, switch mode power supplies.

ABSOLUTE MAXIMUM RATINGS(Tc=25°C)

| SYMBOL | MBOL ARAMETER | | UNIT | | |
|---------------------------|---|-----|------|--|--|
| V _{DSS} | Drain-Source Voltage (V _{GS} =0) | 55 | V | | |
| V _{GS} | Gate-Source Voltage | ±20 | V | | |
| ID | Drain Current-continuous@ Tc=25°C | | А | | |
| I _{DM} | Pulse Drain Current | 390 | А | | |
| P _{tot} | Total Dissipation@T _C =25℃ | 200 | W | | |
| Tj | Max. Operating Junction Temperature | 175 | °C | | |
| T _{stg} | Storage Temperature Range -55~175 | | °C | | |
| • THERMAL CHARACTERISTICS | | | | | |

| THERMAL CHARACTERISTICS | | | | |
|-------------------------|--------------------------------------|------|------|--|
| SYMBOL | PARAMETER | MAX | UNIT | |
| R _{th j-c} | Thermal Resistance, Junction to Case | 0.75 | °C/W | |





| | DIM | MIN | MAA | |
|---|-----|-------|-------|-----|
| | Α | 10 | | |
| | В | 6.6 | 6.8 | 1 |
| | С | 15.23 | 15.25 | |
| | D | 10.15 | 10.17 | |
| | F | 0.76 | 0.78 | |
| | G | 1.26 | 1.28 | |
| | Н | 1.4 | 1.6 | |
| | J | 1.33 | 1.35 | |
| | K | 0.4 | 0.6 | - a |
| | L | 4.6 | 4.8 | |
| | 0 | 8.69 | 8.71 | |
| | R | 5.28 | 5.30 | 1 |
| 1 | S | 1.26 | 1.28 | 1 |
| | U | 0.0 | 0.2 |] |
| | V | 0.37 | 0.39 | |
| | W | 2.80 | 2.82 | 1 |

isc website: <u>www.iscsemi.com</u>



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| • | ELECTRICAL | CHARACTERISTICS | (Tc=25℃) |
|---|------------|------------------------|----------|
|---|------------|------------------------|----------|

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYPE | МАХ | UNIT |
|----------------------|---------------------------------|---|-----|------|------|------|
| V _{(BR)DSS} | Drain-Source Breakdown Voltage | V _{GS} = 0; I _D = 250µA | 55 | | | V |
| V _{GS(th)} | Gate Threshold Voltage | V_{DS} = V_{GS} ; I_D =250 μ A | 2.0 | | 4.0 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D =62A | | | 8 | mΩ |
| I _{GSS} | Gate-Body Leakage Current | V _{GS} = ±20V;V _{DS} = 0 | | | ±100 | nA |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =55V; V _{GS} = 0 | | | 25 | μA |
| Vsd | Diode Forward On-Voltage | Is=62A ;V _{GS} = 0 | | | 1.3 | V |

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